

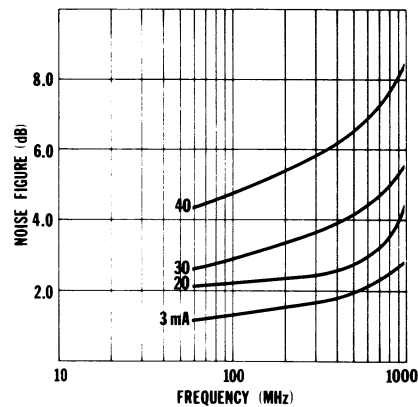
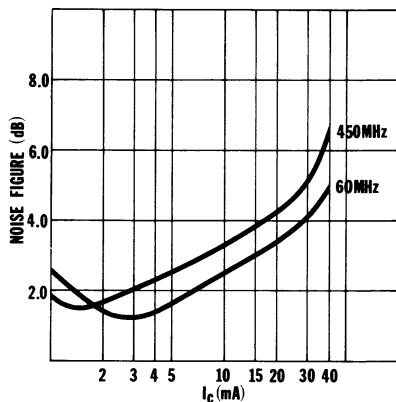
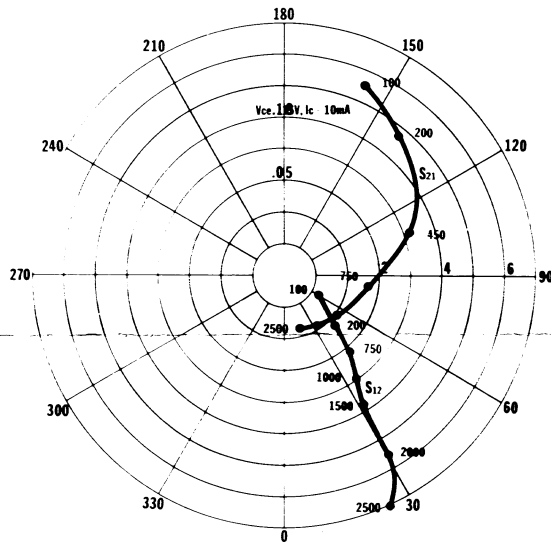
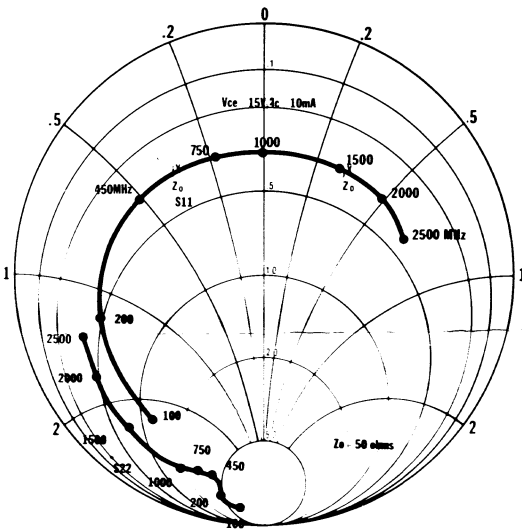
55 Geometry

2N5651

Type	N.F. (dB)	I _c (mA)	Gain (dB)	1dB Compression Point (dBm)		F _L Typ. (MHz)	Test Frequency (MHz)
				Min. N.F.	Typ.		
K5510	1.7	1.5	13	-10	+10	2500	450
2N5651	2.0	3.0	13	-5	+10	2500	450
2N5652	2.5	3.0	13	-5	+10	2300	450
KD5525	3.0	3.0	10	-9	+10	2600	1000
KD5527	3.7	3.0	10	-9	+10	2500	1000
KD5526	4.5	3.0	10	-7	+10	2300	1000

Notes: 1. Gain is specified at min. N.F. Tuning for max: gain typically yields 4.0 to 6.0 as increases

max 40mA 20V/2.5V hFE > 20 / 1V/3mA α₁ = 9F/70V

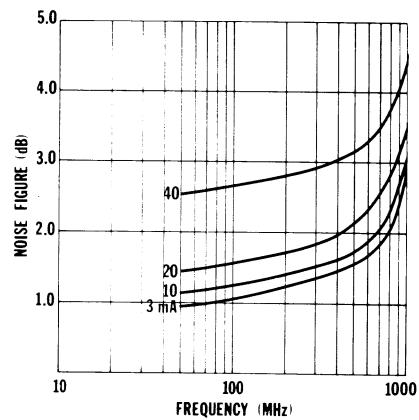
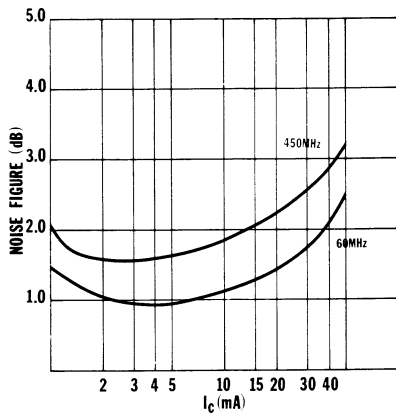
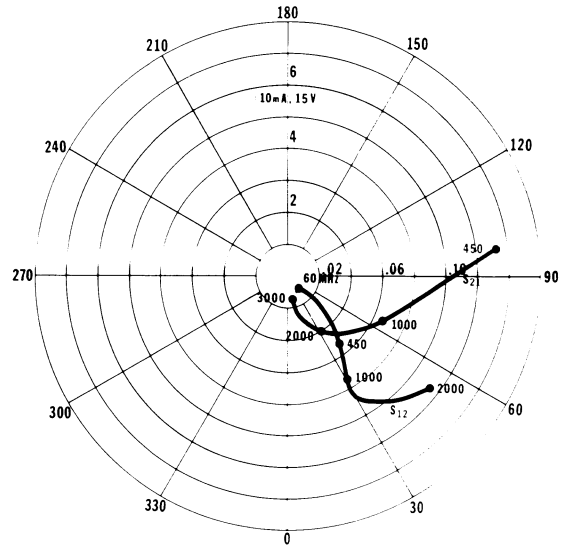
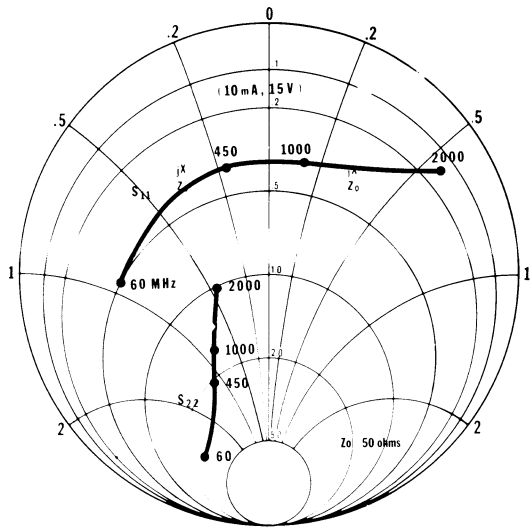


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60 Geometry

Type	N.F. (dB)	I _c (mA)	Gain (dB)	1dB Compression Point (dBm)		Fl. Typ. (MHz)	Test Frequency (MHz)
				Min. N.F.	Typ.		
K6001	1.0	5.0	20	0	+16	3000	60
K6002	1.5	5.0	20	0	+16	2800	60
K6003	2.0	5.0	20	0	+16	2500	60
K6007	1.6	5.0	10	0	+16	3000	450
K6011	1.5	20	20	+12	+20	3000	60
K6012	2.0	20	20	+12	+20	3000	60
K6021	3.0	20	18	+12	+20	3000	450
K6022	3.5	20	18	+12	+20	3000	450
KD6061	4.5	60	16	+22	+27	2400	450
KD6042	5.0	60	16	+22	+27	2400	450

Notes: 1. Gain is specified at min. N.F. Tuning for max: gain typically yields 4.0 to 6.0 as increases





TRANSISTOR SPECIFICATIONS

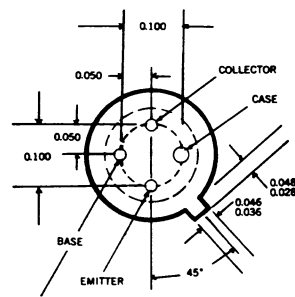
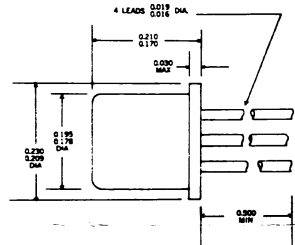
GENERAL DESCRIPTION:

The KMC 2N5652 is a double-diffused, NPN Silicon transistor designed for low-level, low noise UHF amplifier applications. Exceptional performance in Converter and Oscillator circuitry in the UHF range is also a feature of this device.

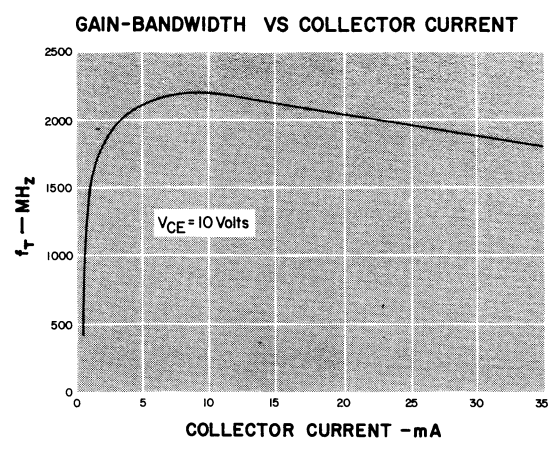
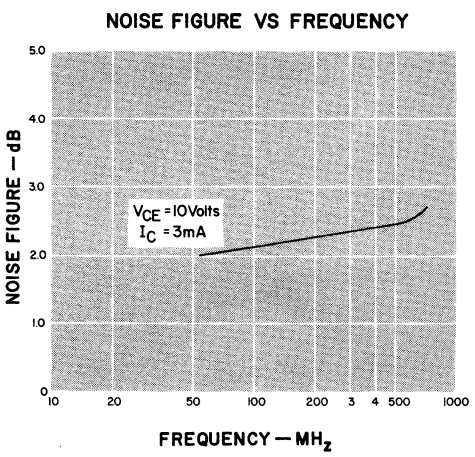
A TO-72 package having a fourth lead connected to the case for grounding and shielding purposes is used. All active elements are isolated from the case.

ABSOLUTE MAXIMUM RATINGS:

Collector to Base Voltage, V_{cbo}	20 volts
Collector to Emitter Voltage, V_{ceo}	15 volts
Emitter to Base Voltage, V_{cbo}	3 volts
Collector Current, I_c	30 mA
Dissipation at 25°C Ambient temperature	150 mw.
Operating junction temperature	200 °C
Storage junction temperature	-65 to +200 °C



All elements isolated from case... fourth lead grounded to case.



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2N5652

ELECTRICAL PARAMETERS AT 25°C

SYMBOL	PARAMETER	TEST CONDITIONS	MIN.	MAX.	UNITS
BV_{CBO}	collector-base breakdown	$I_C = 10 \mu a$	20	—	volts
BV_{EBO}	emitter-base breakdown	$I_E = 10 \mu a$	3	—	volts
I_{CBO}	collector cutoff current	$V_{CB} = 10$ volts	—	.05	μa
h_{FE}	current transfer ratio	$I_C = 3$ mA, $V_{CE} = 10$ v	30	300	—
Ft	Gain-Bandwidth product	$I_C = 3$ mA, $V_{CE} = 10$ v	2000		MHz
C_{cb}	Output capacitance guarded measurement	$V_{CB} = 10$	—	0.7	pf
G_{pe}	small signal power gain	$f = 500$ MHz, $V_{CE} = 10$ v $I_C = 3$ mA	20	—	dB
NF	Noise figure	$I_C = 3$ mA, $V_{CE} = 10$ v $f = 500$ MHz	—	2.5	dB

